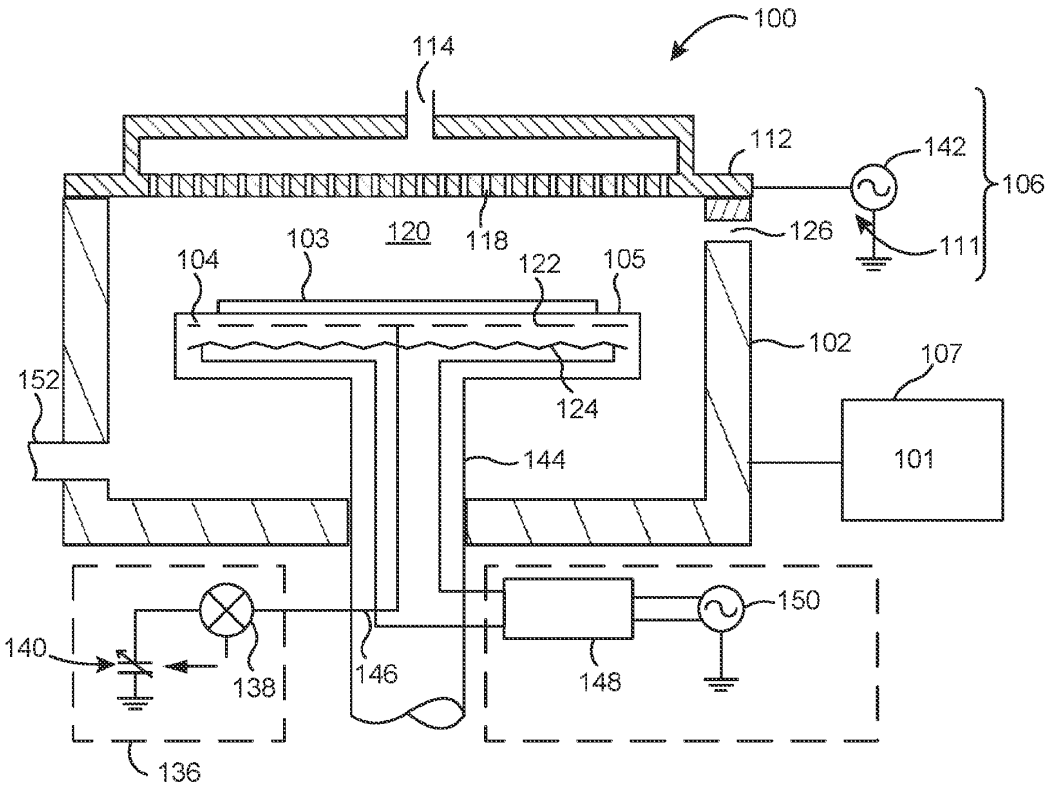

100
114
112
142
106
111
126
120
118
103
104
122
105
102
107
152
124
144
101
150
140
138
146
148
136

FIG. 1

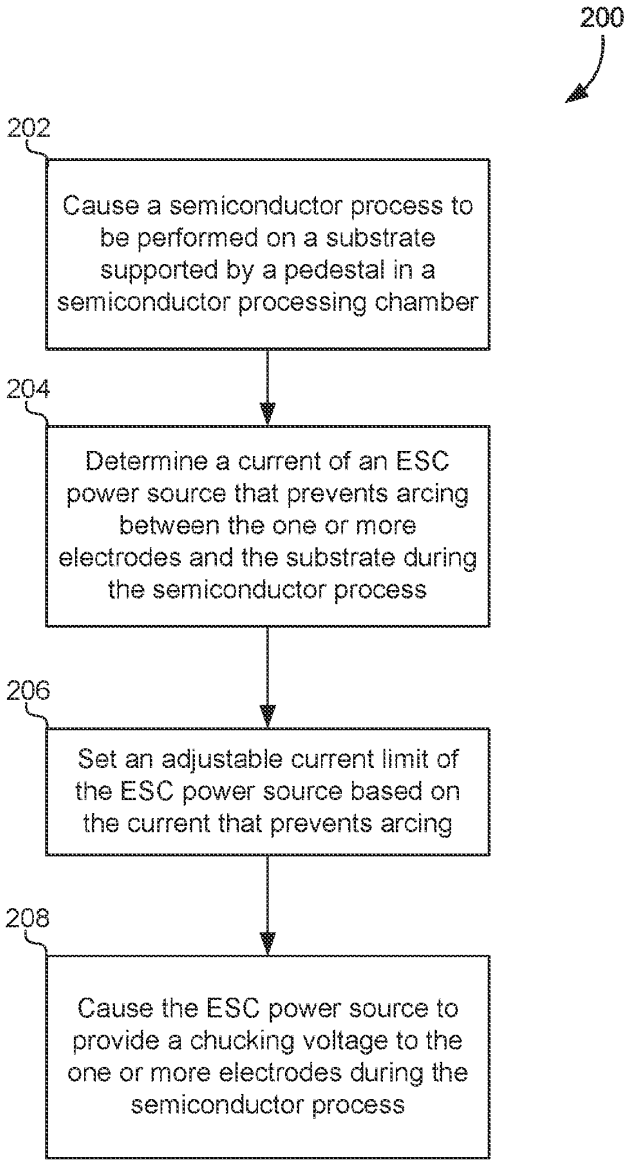

200
202
Cause a semiconductor process to be performed on a substrate supported by a pedestal in a semiconductor processing chamber
204
Determine a current of an ESC power source that prevents arcing between the one or more electrodes and the substrate during the semiconductor process
206
Set an adjustable current limit of the ESC power source based on the current that prevents arcing
208
Cause the ESC power source to provide a chucking voltage to the one or more electrodes during the semiconductor process

FIG. 2

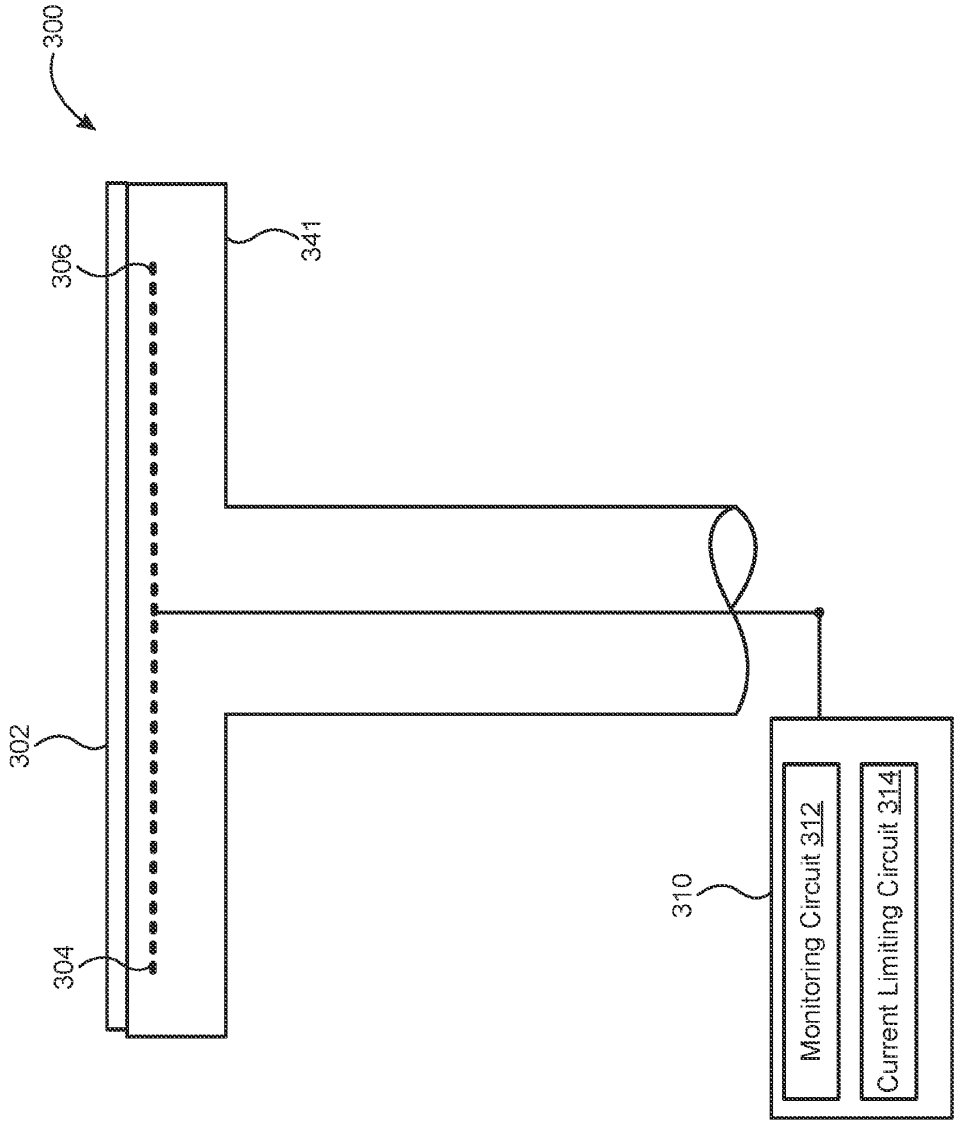

300
306
341
302
304
310
Monitoring Circuit 312
Current Limiting Circuit 314

FIG. 3

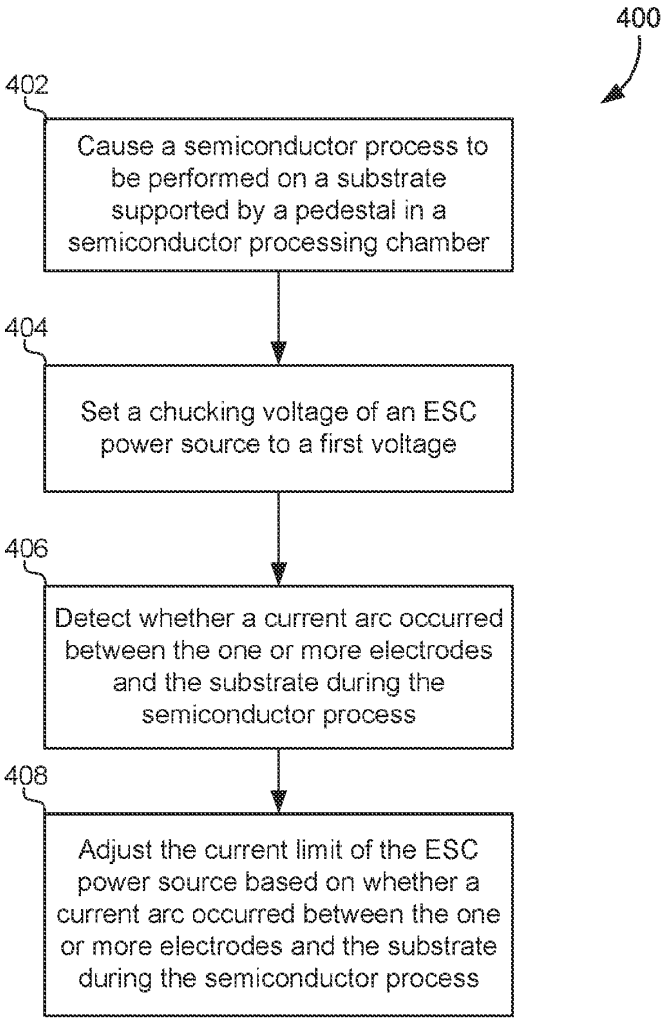

400
402
Cause a semiconductor process to be performed on a substrate supported by a pedestal in a semiconductor processing chamber
404
Set a chucking voltage of an ESC power source to a first voltage
406
Detect whether a current arc occurred between the one or more electrodes and the substrate during the semiconductor process
408
Adjust the current limit of the ESC power source based on whether a current arc occurred between the one or more electrodes and the substrate during the semiconductor process

FIG. 4

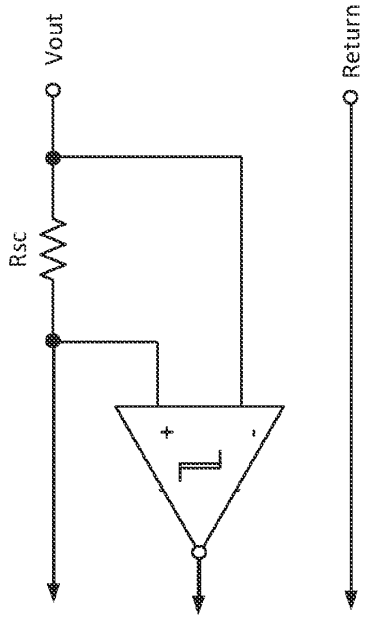



FIG. 5B

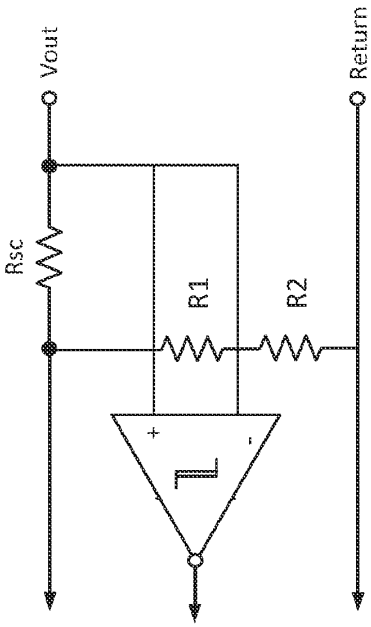



FIG. 5A

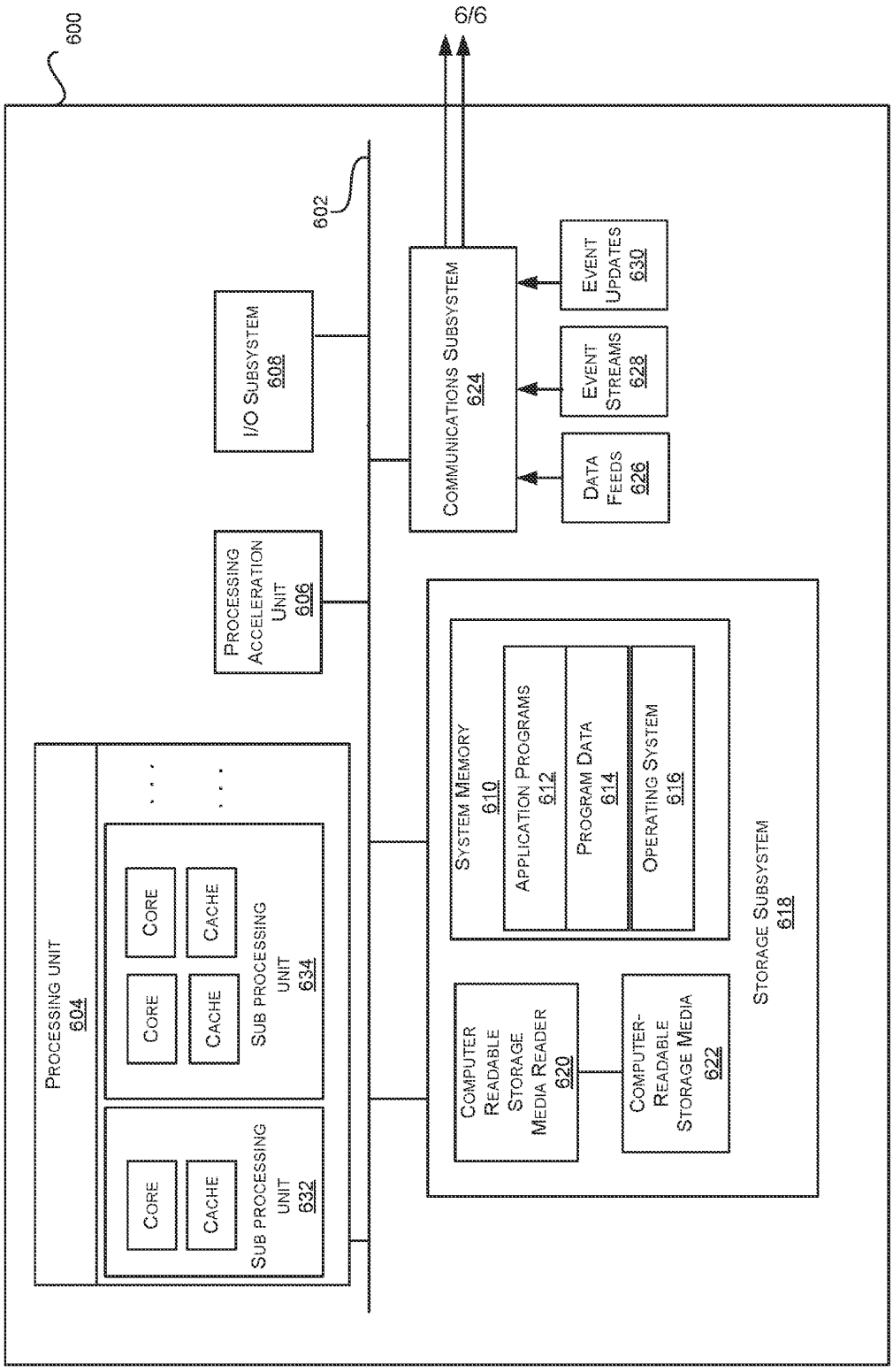

600
6/6
602
I/O SUBSYSTEM 608
COMMUNICATIONS SUBSYSTEM 624
EVENT UPDATES 630
EVENT STREAMS 628
DATA FEEDS 626
PROCESSING ACCELERATION UNIT 606
PROCESSING UNIT 604
SUB PROCESSING UNIT 632
CORE
CACHE
SUB PROCESSING UNIT 634
CORE
CACHE
SYSTEM MEMORY 610
APPLICATION PROGRAMS 612
PROGRAM DATA 614
OPERATING SYSTEM 616
COMPUTER READABLE STORAGE MEDIA READER 620
COMPUTER-READABLE STORAGE MEDIA 622
STORAGE SUBSYSTEM 618

FIG. 6